SPE10S60H-A

主要参数 MAIN CHARACTERISTICS

600V/10A 3 相全桥驱动	
V_{CES}	600V
I_C	10A
V_{ISO}	1500V

封装 **Package**

DIP26-FP

用途 APPLICATIONS

- 风机 Fan motor
- 水泵 Water pump
- 冰箱 Refrigerator

产品特性

- 600V/10A 三相逆变器，内置低损耗沟道栅-场截止型 IGBT。
- 信号高电平有效，兼容 3.3V 和 5V 的 MCU。
- 内置自举二极管。
- 内置欠压保护、过流保护。
- 使能关断功能。
- 恒流温度检测输出。

FEATURES

- 600V/10A three-phase inverter with built-in low-loss trench. gate-field stop IGBT.
- Signal high level active, compatible with 3.3v and 5V MCU.
- Built-in bootstrap diode.
- Built-in undervoltage protection、Over current protection.
- Shut-Down Input.
- Constant current temperature detection output.

订货信息 ORDER MESSAGE

订 货 料 号 Order number	产 品 信 息 Product information			
	无卤-条管 Halogen-Free-Tube	无卤-编带 Halogen-Free-Reel	印 记 Marking	封 装 Package
2A01-0853	SPE10S60H-A	N/A	SPE10S60H-A	DIP26-FP

模块分布示意图 Module distribution diagram

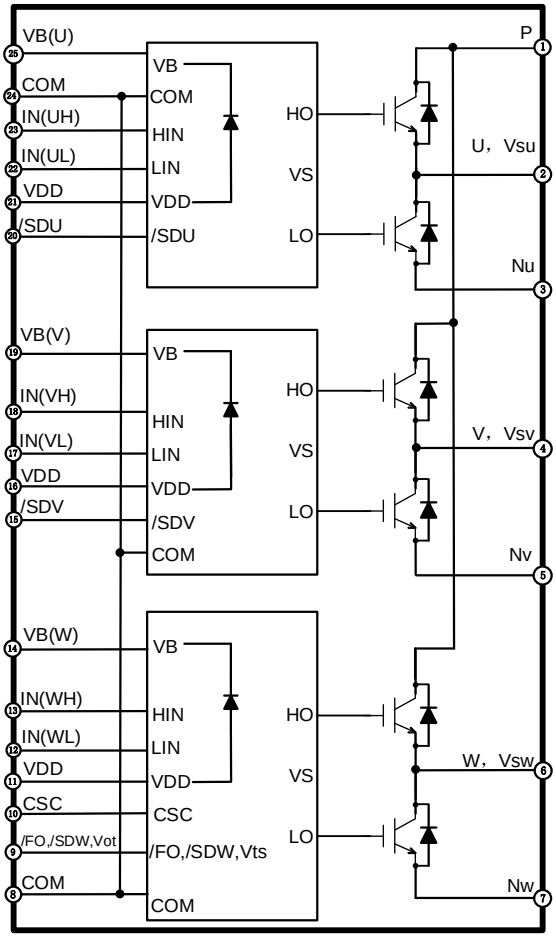

图 1：模块内部电路示意图

Fig 1: Internal circuit

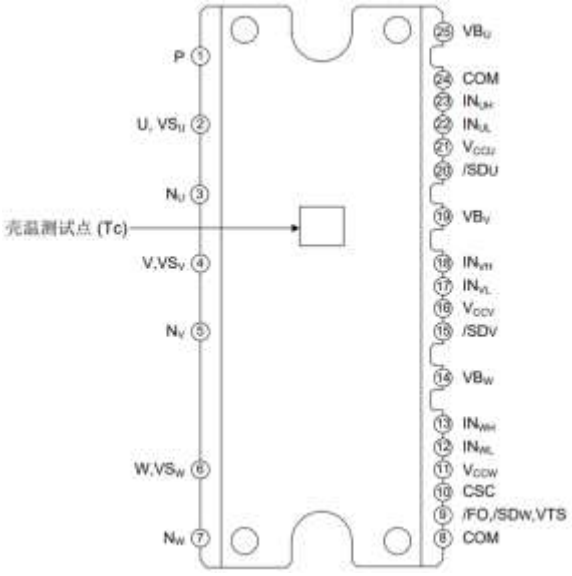

图 2：模块引脚分布示意图

Fig 2: Distribution of pin

引脚编号 Number	引脚名称 Name	引脚描述 Description
1	P	逆变器直流输入端子 DC input terminal of inverter
2	U, VS_U	U 相输出和 U 相高侧驱动偏置电压地 Output for U-Phase & Bias Voltage Ground for U-phase High-Side Driving
3	N_U	U 相下臂 IGBT 发射极端子 U phase lower arm IGBT emitter terminal
4	V, VS_V	V 相输出和 V 相高侧驱动偏置电压地 Output for V-Phase & Bias Voltage Ground for V-phase High-Side Driving
5	N_V	V 相下臂 IGBT 发射极端子 V phase lower arm IGBT emitter terminal
6	W, VS_W	W 相输出和 W 相高侧驱动偏置电压地 Output for W-Phase & Bias Voltage Ground for W-phase High-Side Driving
7	N_W	W 相下臂 IGBT 发射极端子 W phase lower arm IGBT emitter terminal
8	COM	公共电源接地 GND Common Supply Ground
9	/FO, /SDW,VOT	故障输出，W 相输入关闭，温度输出 Fault Output, Shut-Down Input for W Phase, Temperature Output
10	CSC	过流和短路保护关闭输入端子 Shut Down Input for Over Current and Short Circuit Protection
11	V_{CCW}	控制电源端子 Control power terminal
12	IN_{WL}	W 相下臂控制信号输入端子 W phase lower arm control signal input terminal
13	IN_{WH}	W 相上臂控制信号输入端子 W phase upper arm control signal input terminal
14	VB_W	W 相上臂驱动电源端子 W phase upper arm drive power terminal
15	$/SD_V$	V 相输入关闭 Shut-Down Input for V Phase
16	V_{CCV}	控制电源端子 Control power terminal
17	IN_{VL}	V 相下臂控制信号输入端子 V phase lower arm control signal input terminal
18	IN_{VH}	V 相上臂控制信号输入端子 V phase upper arm control signal input terminal
19	VB_V	V 相上臂驱动电源端子 V phase upper arm drive power terminal
20	$/SD_U$	U 相输入关闭 Shut-Down Input for U Phase
21	V_{CCU}	控制电源端子 Control power terminal
22	IN_{UL}	U 相下臂控制信号输入端子 U-phase lower arm control signal input terminal
23	IN_{UH}	U 相上臂控制信号输入端子 U-phase upper arm control signal input terminal
24	COM	公共电源接地 GND Common Supply Ground
25	VB_U	U 相上臂驱动电源端子 U-phase upper arm drive power terminal

图 3：模块引脚功能定义表

Fig 3: Pin function

最大额定值（T_j= 25℃,除非特殊说明）

Absolute Maximum Ratings （T_j= 25℃, Unless otherwise Specified）

逆变部分 Inverter Part

记号 Symbol	参数 Parameter	条件 Condition	额定值 Ratings	单位 Units
V_{PN}	电源电压 Power supply voltage	应用于 P- NU, NV, NW 之间 Applied between P- NU, NV, NW	450	V
$V_{PN(Surge)}$	电源电压（含浪涌） Power supply voltage (including surge)	应用于 P- NU, NV, NW 之间 Applied between P- NU, NV, NW	500	V
V_{CES}	集电极-发射极之间电压 Collector emitter Voltage of Each IGBT		600	V
$\pm I_C$	集电极电流 Each IGBT Current, Continuous	T_C= 25°C, T_C= 100°C	10 5	A A
$\pm I_{CP}$	集电极电流（峰值） Each IGBT Pulse Current, Peak	T_C= 25°C, 脉冲宽度小于 1ms TC=25℃，Less than 1mS	20	A
P_C	集电极功耗 Maximum Power Dissipation	T_C = 25°C， 单晶片 T_C = 25°C，Each IGBT	26	W
T_J	结温 Junction Temperature	(见备注 1) Note1	-40~150	°C

控制部分 Control Part

记号 Symbol	参数 Parameter	条件 Condition	额定值 Ratings	单位 Units
V_{CC}	控制电源电压 Control Supply Voltage	VCC-COM 之间 Applied between VCC and COM	20	V
V_{BS}	高侧控制电压 High-side Bias Voltage	VB-VS 之间 Applied between VB and VS	20	V
V_{IN}	输入信号电压 Input Signal Voltage	VIN-COM 之间 Applied between VIN and COM	-0.3~V_{CC}+0.3	V
I_{FO}	故障输出电流 Fault output current	FO 端子吸入电流值 FO terminal sink current value	1.5	mA
V_{SC}	电流检测端输入电压 Input voltage of current detection terminal	应用于 CSC– COM 之间 Applied between CSC-COM	-0.3~VD+0.3	V
V_{FO}	故障输出电压 Fault output voltage	应用于 FO – COM之间 Applied between FO-COM	-0.3~VD+0.3	V

整个系统 Total System

记号 Symbol	参数 Parameter	条件 Condition	额定值 Ratings	单位 Units
$V_{PN(PROT)}$	自我保护电源电压限制 Self-protecting power supply voltage limit	V_{CC}=V_{BS}=13.5V~16.5V, T_J=125°C, 非重复性, ＜2us	400	V
T_C	模块壳体工作温度 Module shell temperature	-	-20~100	℃
T_{STG}	贮存温度 Storage Temperature	-	-40~125	℃

V_{ISO}	绝缘耐压 Isolation Voltage	60Hz，正弦，AC 1 分钟，连接管脚到散热器 60Hz, Sinusoidal,AC 1 min,between pins and heat-sink plate	1500	Vrms
T	安装力矩 Mounting Torque	安装螺丝：M3	0.6	N.m

备注 1：IPM 功率晶片最大额定结温为 150° C(@表面温度 TC≤ 100° C)。然而,为了确保 IPM 运行安全，结温应限定于 Tj(av) ≤ 125° C (@表面温度 Tc ≤ 100° C)。

Note 1： The maximum rated junction temperature of the IPM power chip is 150° C (@surface temperature TC ≤ 100° C). However, to ensure safe operation of the IPM, the junction temperature should be limited to Tj(av) ≤ 125° C (@surface temperature TC≤ 100° C)

热阻 Thermal Resistance

记号 Symbol	参数 Parameter	条件 Condition	额定值 Ratings	单位 Units
$R_{th(j-c)Q}$	结到外壳的热阻 Junction to Case Thermal resistance	逆变器工作条件下的单个IGBT Each IGBT	4.8	℃/W
$R_{th(j-c)F}$	结到外壳的热阻 Junction to Case Thermal resistance	逆变器工作条件下的单个FRD Each FRD	6.0	℃/W

备注 2: 关于壳体温度（TC）的测量点，参见图 2。

Note 2: For the measurement point of shell temperature (TC), see Figure 2.

电气特性 (Tj=25℃, 除非特殊说明)

Electrical Characteristics (TJ=25℃, Unless Otherwise Specified)

逆变部分 Inverter Part

记号 Symbol	参数 Parameter	条件 Condition		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$V_{CE(SAT)}$	集电极-发射极间饱和电压 Collector - emitter saturation voltage	V_{CC}=V_{BS}=15V, V_{IN}=5V	I_C=10A, T_J=25°C,	-	1.8	2.2	V
			I_C=10A, T_J=125°C,	-	2.0	-	
V_F	FRD正向电压 FRD Forward voltage	V_{IN}= 0V, IC=-10A,		-	1.7	2.2	V
I_{CES}	集电极-发射极间漏电流 Collector emitter leakage current	V_{CE}=V_{CES}		-	-	250	uA
t_{ON}	开关时间（备注3） Switching Times(Note 3)	V_{PN}= 300 V, V_D= V_{DB}= 15 V, I_C=10 A V_{IN}= 0 V ↔5 V, 电感负载 / Inductive Load		-	450	-	nS
$t_{C(ON)}$				-	120	-	
t_{OFF}				-	750	-	
$t_{C(OFF)}$				-	75	-	
t_{rr}				-	100	-	

备注 3：t_{ON} 和 t_{OFF} 包括驱动 IC 内部传输延迟时间。 $t_{C(ON)}$) 和 $t_{C(OFF)}$ 是 IGBT 自身被内部给定门极驱动条件下的开关时间。详见图 3。

Note 3: t_{ON} and t_{OFF} include the internal propagation delay time of the driver IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching times of the IGBT itself driven by the internally given gate. See Figure 3 for details.

控制部分 Control Part

记号 Symbol	参数 Parameter	条件 Condition		最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{QCC}	VCC 静态电流 Quiescent VCC Supply Current	VCC=15V VIN=0V	VCC-COM 之间 Applied between VCC and COM	-	-	1500	uA
I_{QBS}	VBS 静态电流 Quiescent VBS Supply Current	VBS=15V VIN=0V	VB(U)-U，VB(V)-V，VB(W)-W 之间 Applied between VB(U)-U，VB(V)-V，VB(W)-W	-	-	200	uA
V_{FOH}	故障输出电压 Fault Out Voltage	VSC=0V，/FO Circuit：6.8K to 5V pull-up		-	4.25	-	V
V_{FOL}		VSC=1V，/FO Circuit：6.8K to 5V pull-up		-	0.47	-	
$V_{SC(ref)}$	短路跳闸阈值 Short-Circuit Trip Level	V_{CC}=15 V		0.43	0.48	0.53	V
U_{VCCD}	低侧欠压保护(图 5) Low-Side Under-Voltage Protection（Fig 5）	检测电平 Detection Level		9.5	10.5	11.5	V
U_{VCCR}		复位电平 Reset Level		10.5	11.5	12.5	V
U_{VBSD}	高侧欠压保护(图 6) High-Side Under-Voltage Protection（Fig 6）	检测电平 Detection Level		9.5	10	11.5	V
U_{VBSR}		复位电平 Reset Level		10.5	11	12.5	V
T_{FO}	故障输出脉冲宽度 Fault-Out Pulse Width			20	-	-	uS
I_{FO}	温度输出电流 Fault current Temperature Sensing（note4）	Tj=25℃		-	110	-	uA
		Tj=100℃		-	279	-	uA
T_{FO}	温度输出电压 Fault Voltage Temperature Sensing	HVIC温度=25°C，上拉6.8KΩ电阻到5V		-	4.25	-	V
		HVIC温度=100°C，上拉6.8KΩ电阻到5V		-	3.1	-	V
V_{FSDR}	使能关断复位电平 Shut-down Reset level	SDx-COM		1.7	2.0	2.4	V
V_{FSDD}	使能关断阈值电压 Shut-down Detection level	SDx-COM		0.8	1.1	1.5	V
V_{IH}	导通阈值电压 ON Threshold Voltage	逻辑高电平 Logic high level	施加在V_{IN}和COM之间 Applied between Vin-COM	-	-	2.6	V
V_{IL}	关断阈值电压 OFF Threshold Voltage	逻辑低电平 Logic low level		0.8	-	-	V

备注 4：IPM 温度输出电流曲线请参考图 4.2，图 4.2 曲线是以 6.8KΩ上拉电阻至 5V 和以 4.7 KΩ上拉电阻至 3.3V 测试结果。

Note 4: Please refer to figure 4.2 for the temperature output current characteristic curve of IPM. The curve in Figure 4.2 shows the test results of 6.8 KΩ pull-up resistance to 5V and 4.7 KΩ pull-up resistance to 3.3V.

自举二极管部分 Bootstrap Diode Part

V_{F_SDB}	正向压降 Forward voltage drop	IF=1mA，Tc=25℃	-	1.0	1.8	V
R_{BSD}	自举电阻 Bootstrap diode on resistor			100		Ω

推荐工作条件 Recommended Operating Conditions

记号 Symbol	参数 Parameter	条件 Condition	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
V_{PN}	电源电压 Supply Voltage	施加在P和N之间 Between P and N	-	300	400	V
V_{CC}	控制电源电压 Control Supply Voltage	施加在V_{CC}和 COM之间 Between V_{CC} and COM	13.5	15.0	16.5	V
V_{BS}	高端偏压 High-Side Bias Voltage	施加在V_B和V_S之间 Between V_B and V_S	13.5	15.0	16.5	V
d_{VCC}/d_t, d_{VBS}/d_t	控制电源波动 Control power fluctuation	-	-1	-	1	V/us
t_{dead}	防止桥臂直通的死区时间 Blanking Time for Preventing Arm-Short	V_{CC} = V_{BS} = 13.5 ~ 16.5 V, Tj ≤150°C	1.0	-	-	us
$P_{WIN(ON)}$	输入信号最小开启脉宽 Minimum On pulse width of input signal	-	0.7	-	-	us
$P_{WIN(off)}$	输入信号最小关闭脉宽 Minimum Off Pulse Width of Input Signal	-	0.7	-	-	
F_{PWM}	PWM 开关频率 PWM Switching Frequency	Tj ≤150°C	-	-	20	KHz

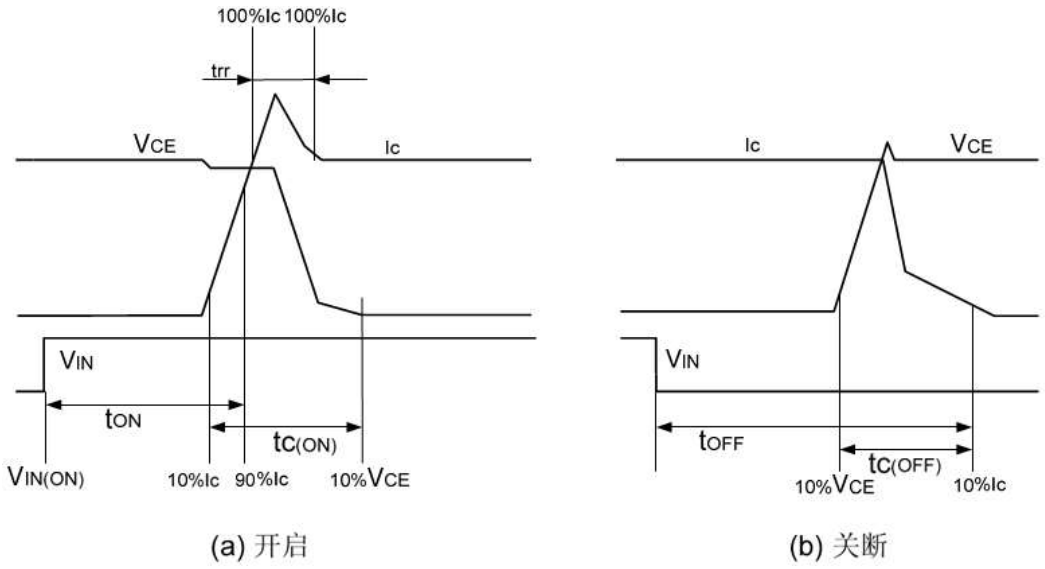

图 4：开关时间定义

Fig 4: Switching Time Definition

IC 温度输出的电流-温度曲线 I-T curve of temperature output of IC

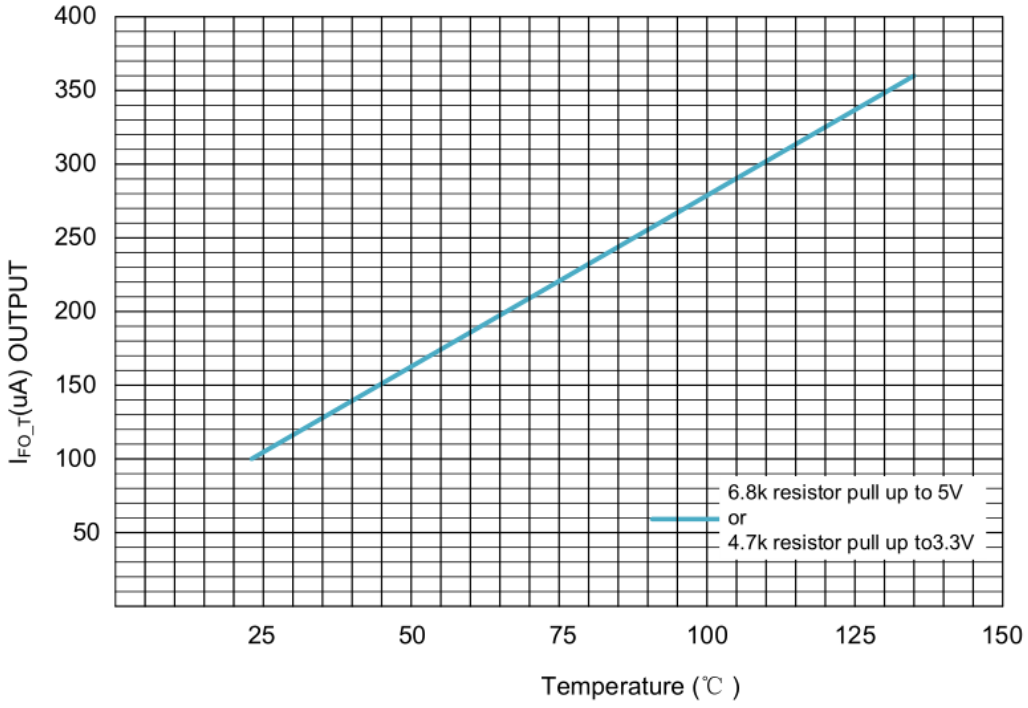

图 5：**IC 温度输出的电流-温度曲线**

Fig 5:I-T curve of temperature output of IC

保护功能时序图 Time Charts of Protective Function

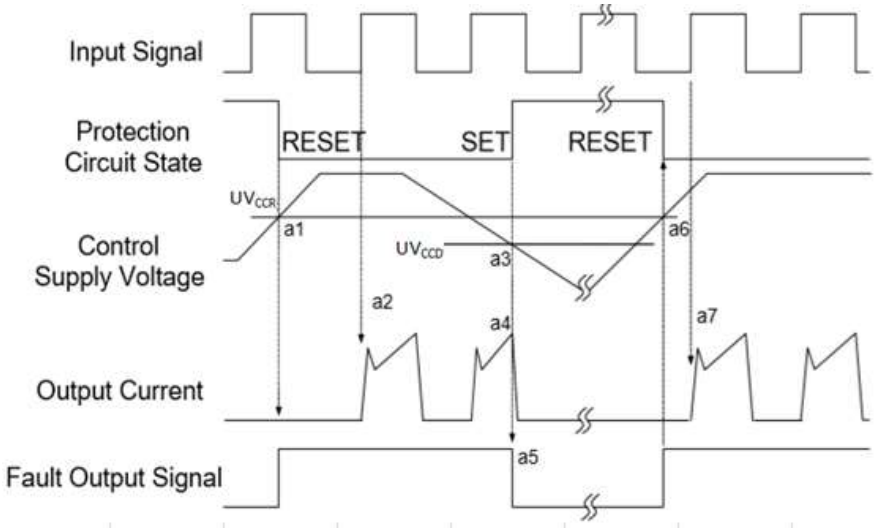

图 6：欠压保护时序图(低侧)

Fig 6：Undervoltage protection sequence diagram (low side)

a1 :电源电压上升：电压上升至 UV_{CCR},当下一个输入信号到来时电路开始工作；

a1 : Control supply voltage rises: after the voltage rises UV_{CCR}, the circuits start to operate when next input is applied.

a2: 正常运行: IGBT 开启并加载电流。

a2: Normal operation: IGBT turns on and loads current.

a3: 欠压检测点(UV_{CCD})。

a3: Undervoltage detection point (UV_{CCD}).

a4: 不管输入是什么信号，IGBT 都是关闭状态。

a4: No matter what signal is input, the IGBT is off.

a5: 故障输出开启。

a5: Fault output is on.

a6: 欠压恢复(UV_{CCR})。

a6: Undervoltage recovery (UV_{CCR}).

a7: 正常运行: IGBT 导通并加载负载电流。

a7: Normal operation: IGBT is turned on and load current is loaded.

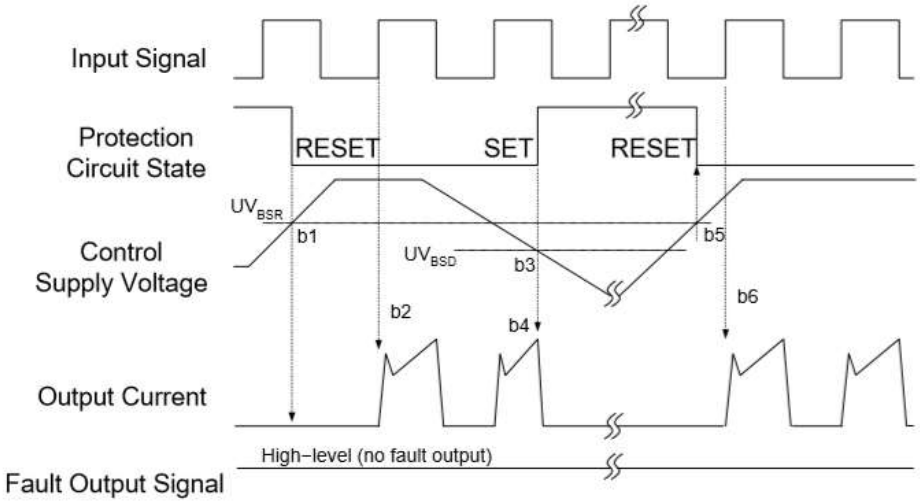

图 7：欠压保护时序图(高侧)

Fig 7：Undervoltage protection sequence diagram (High side)

b1：电源电压上升：当该电压上升到欠压恢复点，在下一个欠压信号被执行前该线路将启动运行。

b1: Power supply voltage rise: When the voltage rises to the undervoltage recovery point, the line will start running before the next undervoltage signal is executed.

b2：正常运行: IGBT 导通并加载负载电流。

b2: Normal operation: IGBT is turned on and load current is applied.

b3：欠压检测 (UV_{BSD})。

b3: Undervoltage detection (UV_{BSD}).

b4：不管输入是什么信号，IGBT 都是关闭状态。

b4: No matter what signal is input, IGBT is off.

b5：欠压恢复(UV_{BSR})。

b5: Undervoltage recovery (UV_{BSR})。.

b6：正常运行: IGBT 导通并加载负载电流。

b6: Normal operation: IGBT is turned on and load current is applied.

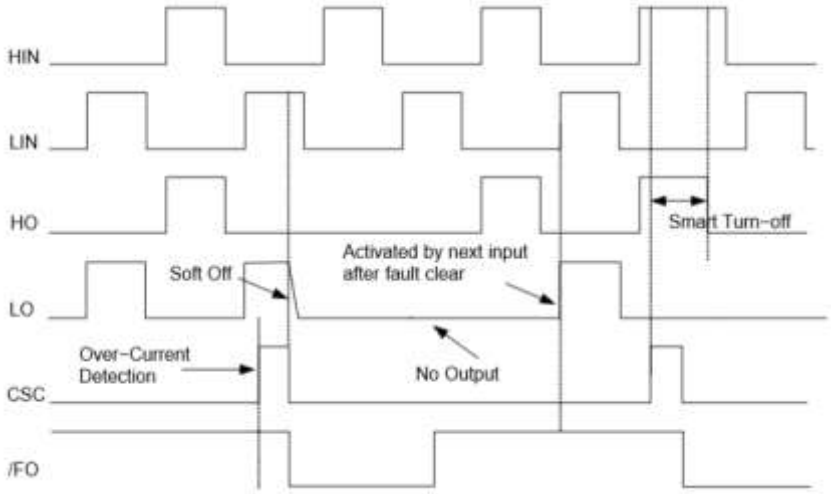

图 8：过流保护时序

Fig8：Fault-Out Function by Over Current Protection

HIN :高侧输入信号；
HIN : High−side Input Signal
LIN : 低侧输入信号；
LIN : Low−side Input Signal
HO : 高侧输出信号；
HO : High−Side Output Signal
LO : 低侧输出信号；
LO : Low−Side Output Signal
CSC :过流侦测信号；
CSC : Over Current Detection Input
/FO:故障输出信号
/FO : Fault Out Function

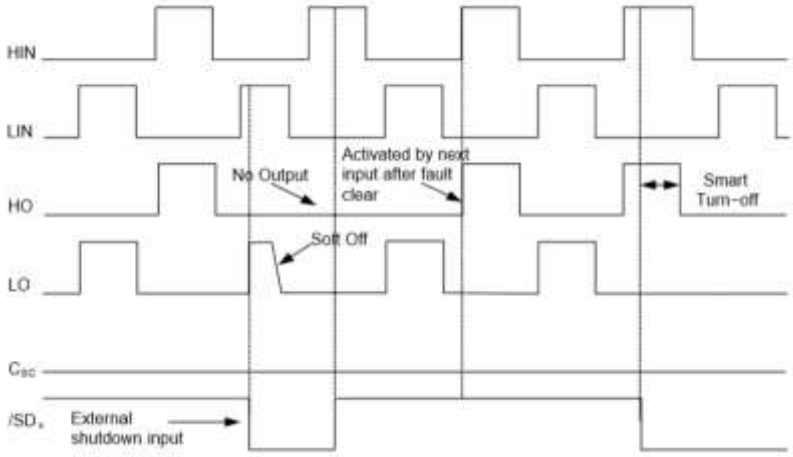

图 9. 外部关断功能时序

Figure 9. Shutdown Input Function by External Command

HIN :高侧输入信号；
HIN : High−side Input Signal
LIN : 低侧输入信号；
LIN : Low−side Input Signal
HO : 高侧输出信号；
HO : High−Side Output Signal
LO : 低侧输出信号；
LO : Low−Side Output Signal
CSC :过流侦测信号；
CSC : Over Current Detection Input
/SDx:外部关断输入信号
/SDx : Shutdown Input Function

输入输出接口电路 **Input/output interface circuit**

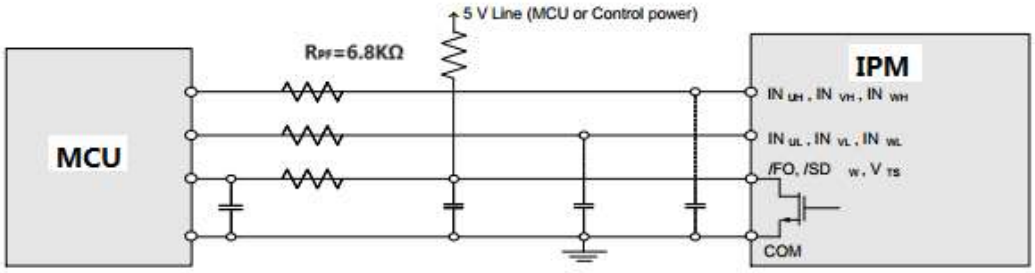

图 10. 推荐的 MCU I/O 接口电路

Figure 10: Recommended MCU input and output interface circuit

备注 5：由于 PWM 的控制方式和实际应用电路的阻抗及线路板的阻抗，RC 去耦可能会有变化。

Note 5 : Due to the PWM control method and the impedance of the actual application circuit and the impedance of the circuit board, RC decoupling may change.

应用电路 Application Circuit

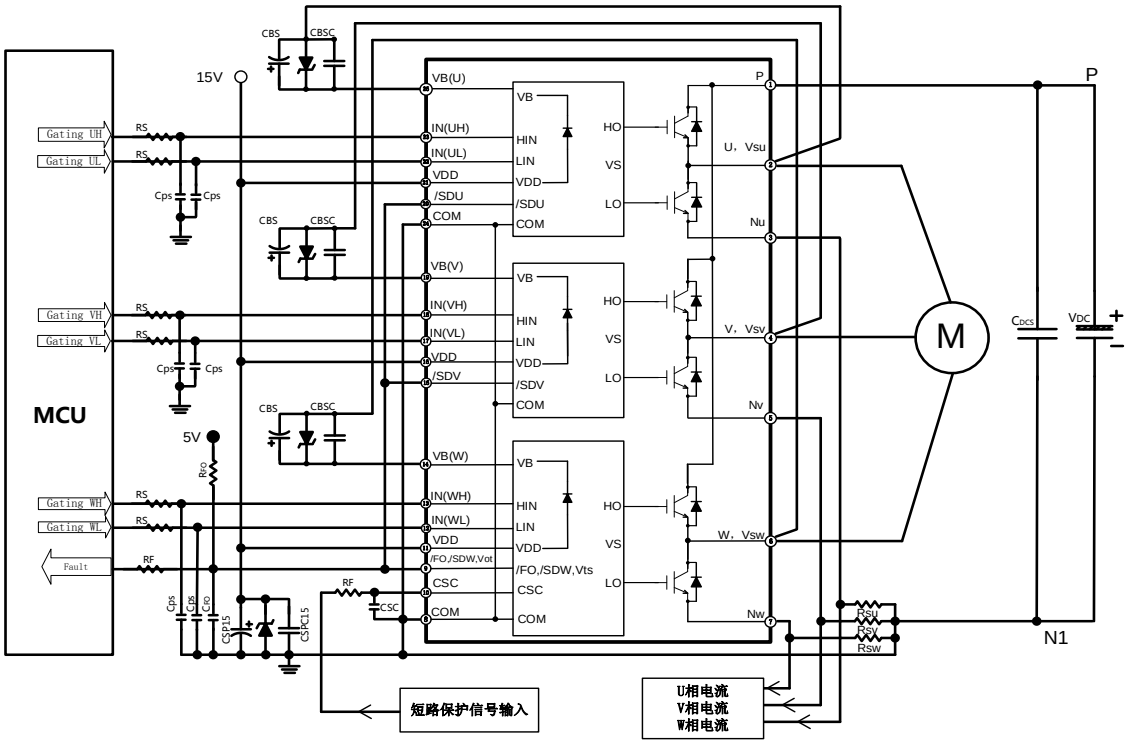

图 11：典型应用电路图

Fig 11：Example of Application Circuit

备注 6：.关于引脚的位置请参阅图 1.

Note 6: Refer to figure 1 for pin location.

备注 7:为避免故障，各输入接线应尽可能短。

Note 7:To avoid malfunction, the wiring of each input should be as short as possible

备注 8:为防止浪涌损坏，PN 之间建议增加一个高频非感性平缓电容（0.1μF～0.22μF）,电容的连线要尽量短。

Note 8:To prevent surge destruction, it is recommended to add a high-frequency non inductive smoothing capacitor （0.1μF～0.22μF）between PN, and the wiring of the capacitor should be as short as possible.

备注 9:输入信号高电平有效，在 HVIC 每个通道的输入端都有一个下拉电阻连接到地；建议在输入端增加 RC 滤波电路来防止输入信号振荡。

Note 9: The high level of the input signal is effective, and a pull-down resistor is connected to the ground at the input terminals of eachchannel of HVIC; It is suggested to add RC filter circuit at the input terminals to prevent input signal oscillation.

备注 10:所有电容的位置尽可能的靠近 IPM。

Note 10: Position all capacitors as close to IPM as possible.

备注 11:控制地线和电源地线要连接在一个点，走线尽量短；

Note 11:The control ground wire and power ground wire shall be connected at one point, and the wiring shall be as short as possible;

备注 12.在短路保护电路，请选择时间常数在 1.5～2us 范围内的 RF 和 CSC,同时 RF 和 CSC 周边的接线都应尽量短，RF 接线应靠近分流电阻；

Note 12:In the short−circuit current protection circuit, please select the RF CSC time constant in the range 1.5～2us,At the same time, the wiring around RF and CSC shall be as short as possible, and RF wiring shall be close to shunt resistance;

备注 13./FO,/SD 的连线尽可能短。

Note 13:/FO and /SD must be connected as short as possible.

外形封装图 Detailed Package Outline Drawings

SPE10S60H-A (DIP26-FP)

单位：mm

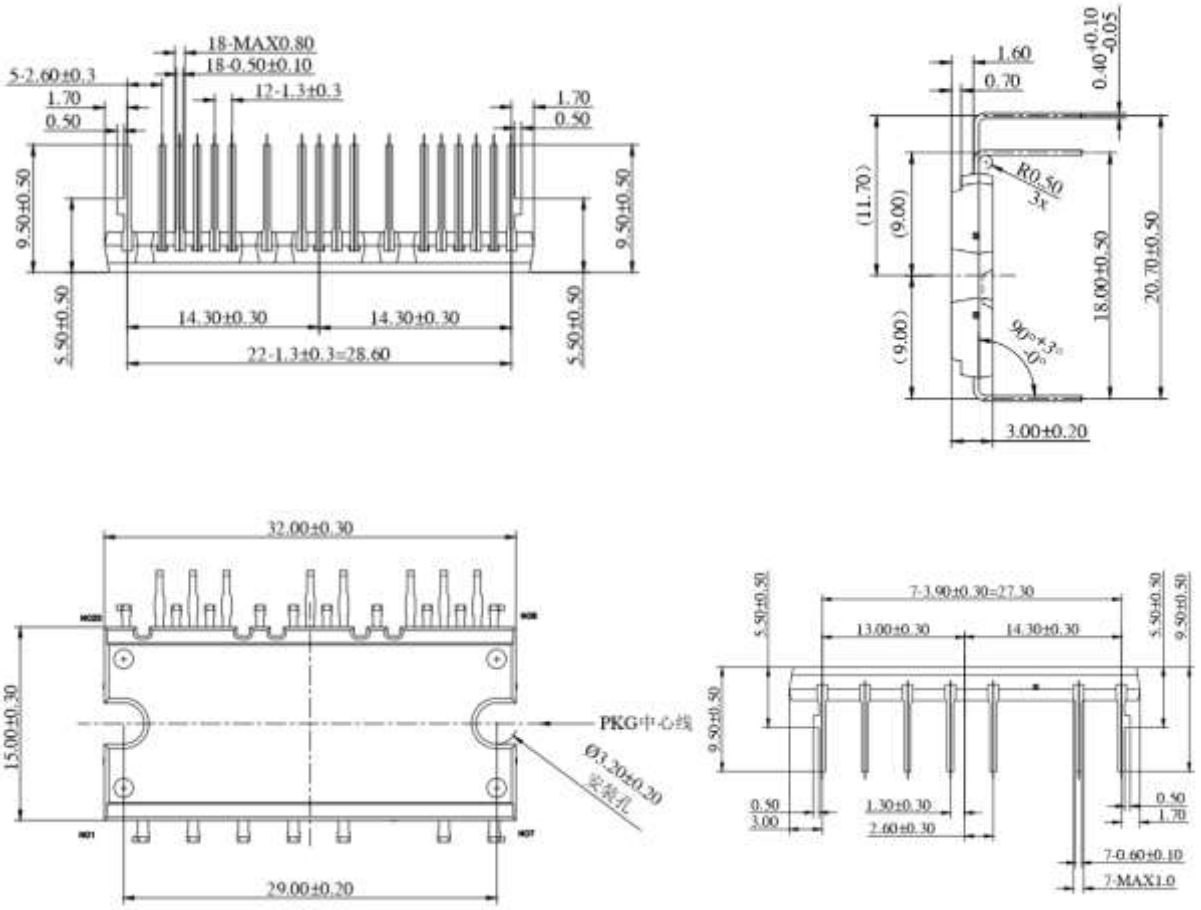

图 12：SPE10S60H-A 封装外形图

Fig 12：SPE10S60H-A Package Outline Drawings

注意事项

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